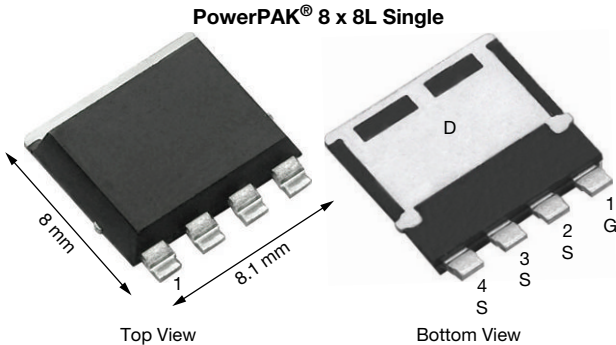


## N-Channel 40 V (D-S) 175 °C MOSFET



### FEATURES

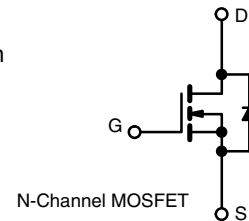
- TrenchFET® Gen IV power MOSFET
- Fully lead (Pb)-free device
- Optimized  $Q_g$ ,  $Q_{gd}$ , and  $Q_{gd}/Q_{gs}$  ratio reduces switching related power loss
- Up to 200 A maximum continuous drain current
- 50 % smaller footprint than D<sup>2</sup>PAK / TO-263
- 100 %  $R_g$  and UIS tested
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

### APPLICATIONS

- Synchronous rectification
- OR-ing
- Motor drive control
- Battery management



PRODUCT SUMMARY	
$V_{DS}$ (V)	40
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 10$ V	0.00096
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 4.5$ V	0.00115
$Q_g$ typ. (nC)	127
$I_D$ (A) <sup>a, g</sup>	200
Configuration	Single

### ORDERING INFORMATION

Package	PowerPAK 8 x 8L
Lead (Pb)-free and halogen-free	SiJH440E-T1-GE3

### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	$V_{DS}$	40	V
Gate-source voltage	$V_{GS}$	+20 / -16	V
Continuous drain current ( $T_J = 150$ °C)	$I_D$	$T_C = 25$ °C	200 <sup>a</sup>
		$T_C = 70$ °C	200 <sup>a</sup>
		$T_A = 25$ °C	40 <sup>b</sup>
		$T_A = 70$ °C	33.8 <sup>b</sup>
Pulsed drain current ( $t = 100$ $\mu$ s)	$I_{DM}$	500	A
Continuous source-drain diode current	$I_S$	$T_C = 25$ °C	160
		$T_A = 25$ °C	2.67 <sup>b, c</sup>
Single pulse avalanche current	$I_{AS}$	60	
Single pulse avalanche energy	$E_{AS}$	180	mJ
Maximum power dissipation	$P_D$	$T_C = 25$ °C	158
		$T_C = 70$ °C	110
		$T_A = 25$ °C	3 <sup>b</sup>
		$T_A = 70$ °C	2.1 <sup>b</sup>
Operating junction and storage temperature range	$T_J, T_{stg}$	-55 to +175	°C
Soldering recommendations (peak temperature) <sup>c</sup>		260	

### THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient <sup>b</sup>	$R_{thJA}$	42	50	°C/W
Maximum junction-to-case (drain)	$R_{thJC}$	0.8	0.95	

#### Notes

- Package limited.
- Surface mounted on 1" x 1" FR4 board.
- $t = 10$  s.
- See solder profile ([www.vishay.com/doc?73257](http://www.vishay.com/doc?73257)). The PowerPAK 8 x 8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- Maximum under steady state conditions is 50 °C/W.
- $T_C = 25$  °C.

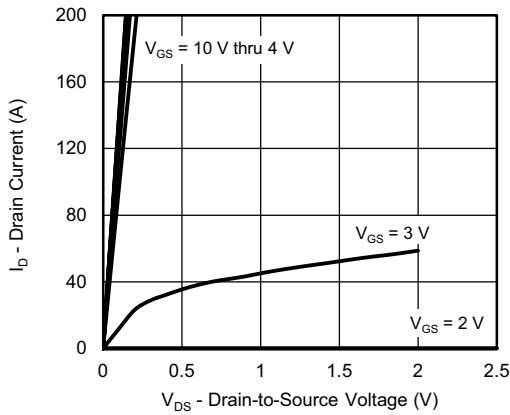
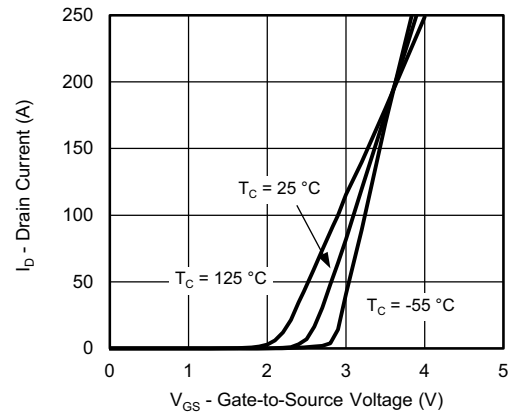
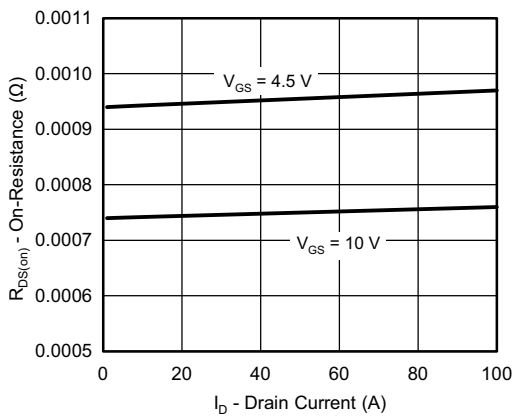
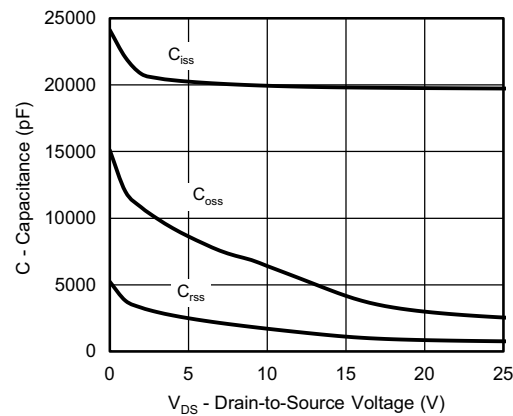
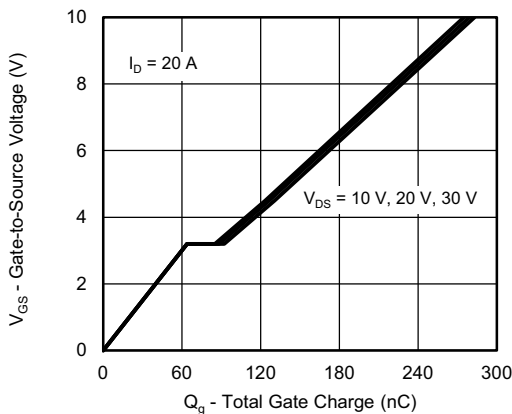
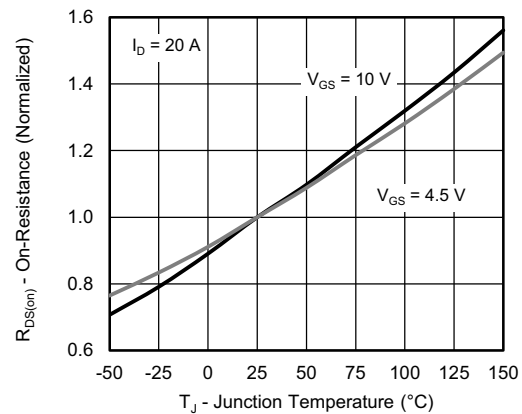


SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-source breakdown voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	40	-	-	V
V <sub>DS</sub> temperature coefficient	ΔV <sub>DS</sub> /T <sub>J</sub>	I <sub>D</sub> = 10 mA	-	24	-	mV/°C
V <sub>GS(th)</sub> temperature coefficient	ΔV <sub>GS(th)</sub> /T <sub>J</sub>	I <sub>D</sub> = 250 μA	-	-6.6	-	
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1	-	2.3	V
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = +20 / -16 V	-	-	100	nA
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 40 V, V <sub>GS</sub> = 0 V	-	-	1	μA
		V <sub>DS</sub> = 40 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 70 °C	-	-	15	
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ 10 V, V <sub>GS</sub> = 10 V	60	-	-	A
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A	-	0.00080	0.00096	Ω
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 20 A	-	0.00096	0.00115	
Forward transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 20 A	-	140	-	S
<b>Dynamic <sup>b</sup></b>						
Input capacitance	C <sub>ISS</sub>	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V, f = 1 MHz	-	20 330	-	pF
Output capacitance	C <sub>OSS</sub>		-	2920	-	
Reverse transfer capacitance	C <sub>RSS</sub>		-	820	-	
Total gate charge	Q <sub>g</sub>	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A	-	279	420	nC
		V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 20 A	-	127	195	
Gate-source charge	Q <sub>gs</sub>		-	64	-	
Gate-drain charge	Q <sub>gd</sub>		-	24.5	-	
Gate resistance	R <sub>g</sub>	f = 1 MHz	0.5	1.7	3.0	Ω
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> = 20 V, R <sub>L</sub> = 10 Ω, I <sub>D</sub> ≅ 20 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 1 Ω	-	28	56	ns
Rise time	t <sub>r</sub>		-	35	70	
Turn-off delay time	t <sub>d(off)</sub>		-	105	210	
Fall time	t <sub>f</sub>		-	30	60	
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> = 20 V, R <sub>L</sub> = 1 Ω, I <sub>D</sub> ≅ 20 A, V <sub>GEN</sub> = 4.5 V, R <sub>g</sub> = 1 Ω	-	140	280	
Rise time	t <sub>r</sub>		-	290	580	
Turn-off delay time	t <sub>d(off)</sub>		-	78	156	
Fall time	t <sub>f</sub>		-	53	106	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous source-drain diode current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	-	-	160	A
Pulse diode forward current	I <sub>SM</sub>		-	-	300	
Body diode voltage	V <sub>SD</sub>	I <sub>S</sub> = 5 A, V <sub>GS</sub> = 0 V	-	0.68	1.1	V
Body diode reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> = 20 A, di/dt = 100 A/μs, T <sub>J</sub> = 25 °C	-	92	184	ns
Body diode reverse recovery charge	Q <sub>rr</sub>		-	245	490	nC
Reverse recovery fall time	t <sub>a</sub>		-	54	-	ns
Reverse recovery rise time	t <sub>b</sub>		-	38	-	

**Notes**

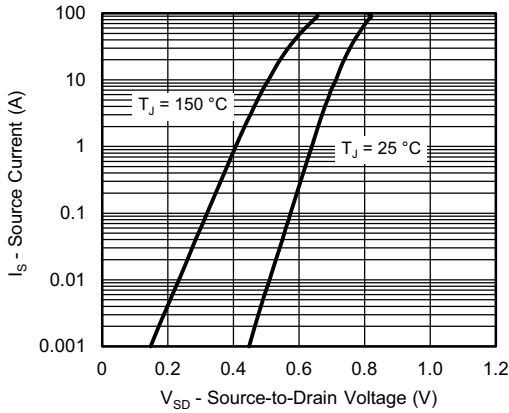
- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

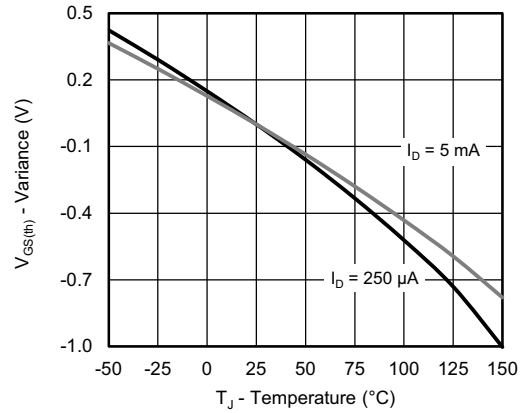
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**Output Characteristics**

**Transfer Characteristics**

**On-Resistance vs. Drain Current and Gate Voltage**

**Capacitance**

**Gate Charge**

**On-Resistance vs. Junction Temperature**



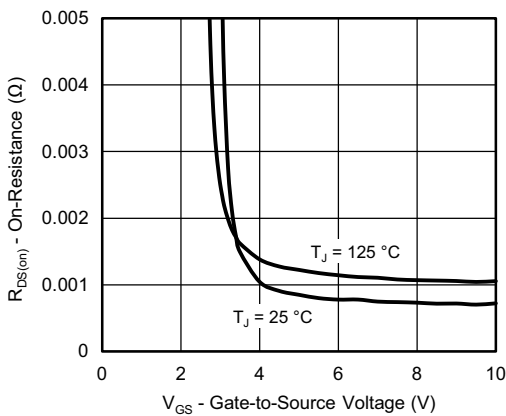
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



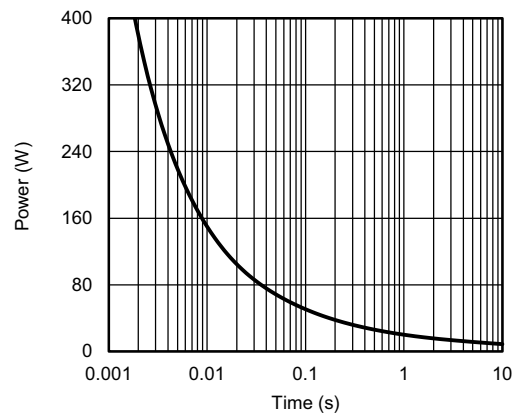
Source-Drain Diode Forward Voltage



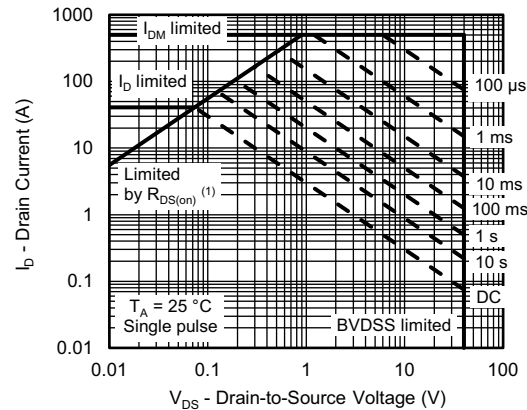
Threshold Voltage



On-Resistance vs. Gate-to-Source Voltage



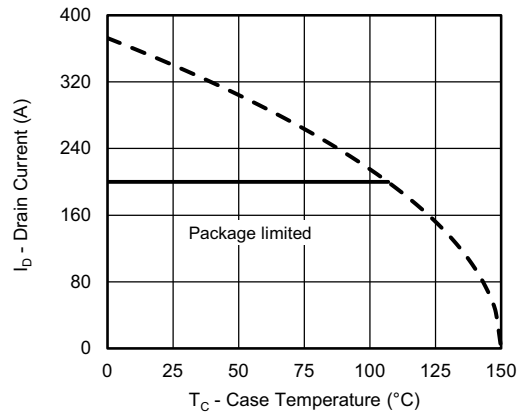
Single Pulse Power, Junction-to-Ambient



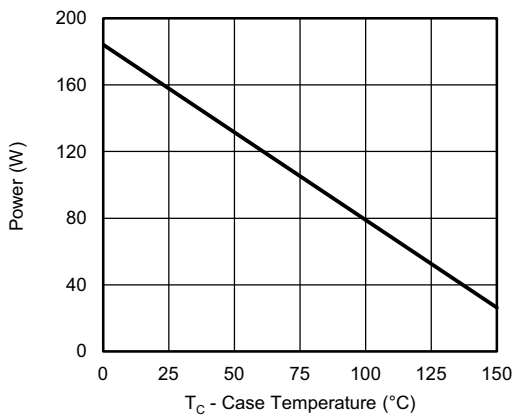
Safe Operating Area, Junction-to-Ambient



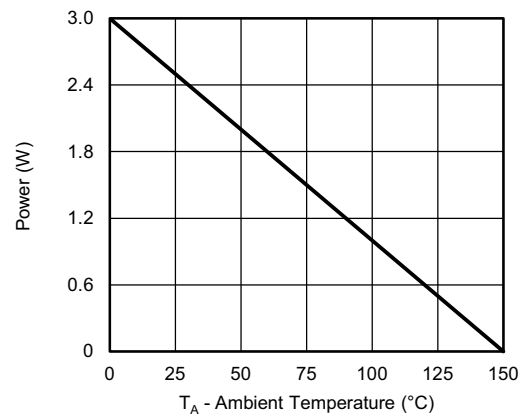
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



**Current Derating <sup>a</sup>**



**Power, Junction-to-Case**



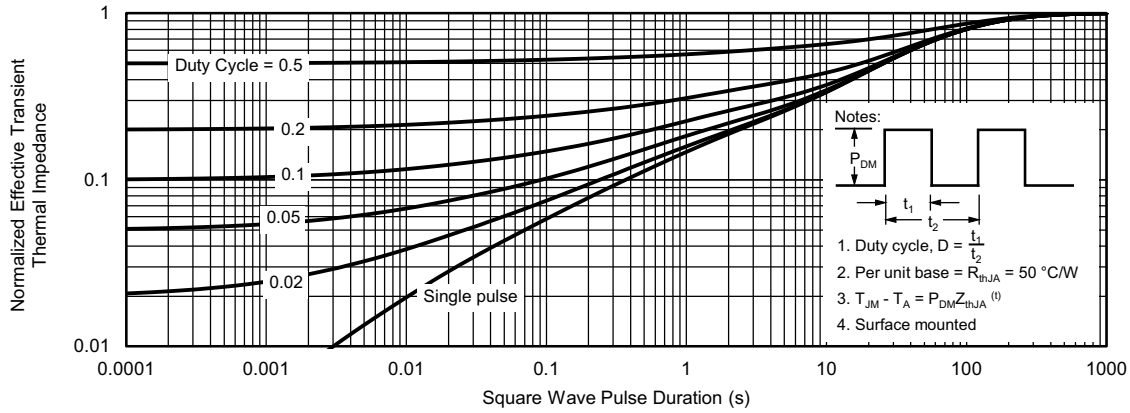
**Power, Junction-to-Ambient**

**Note**

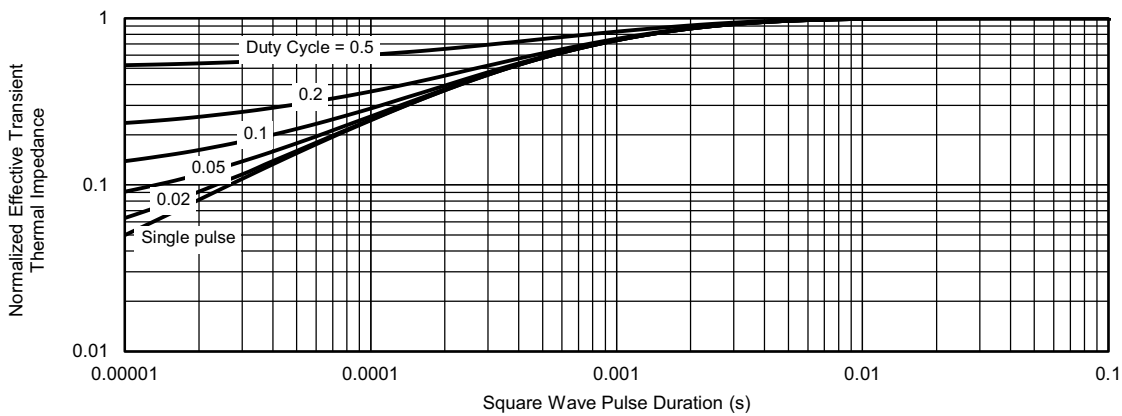
- a. The power dissipation  $P_D$  is based on  $T_J$  max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



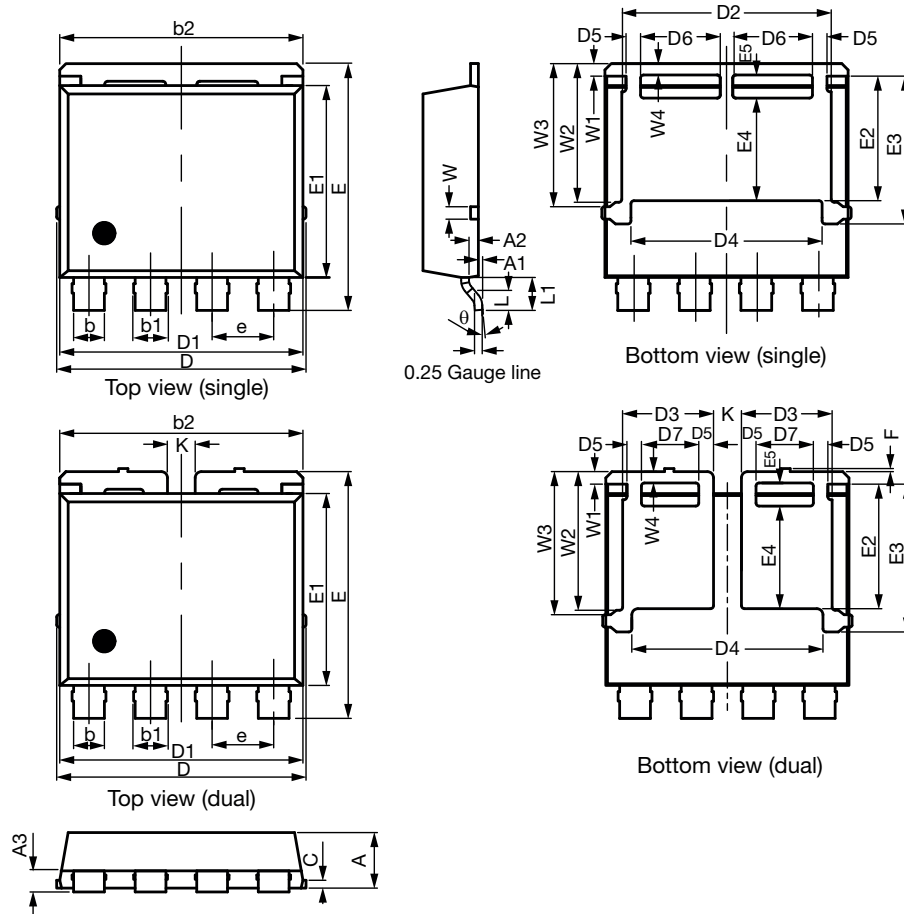
Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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## PowerPAK<sup>®</sup> 8 x 8L Case Outline



DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	1.70	1.80	1.90	0.067	0.071	0.075
A1	0.00	0.08	0.13	0.000	0.003	0.005
A2	0.25	0.30	0.35	0.010	0.012	0.014
A3	0.55	0.62	0.70	0.022	0.024	0.028
b	0.92	1.00	1.08	0.036	0.039	0.043
b1	1.02	1.10	1.18	0.040	0.043	0.046
b2	7.80	7.90	8.00	0.307	0.311	0.315
c	0.20	0.25	0.30	0.008	0.010	0.012
D	8.00	8.10	8.25	0.315	0.319	0.325
D1	7.80	7.90	8.00	0.307	0.311	0.315
D2	6.70	6.80	6.90	0.264	0.268	0.272
D3	2.85	2.95	3.05	0.112	0.116	0.120
D4	6.11	6.21	6.31	0.241	0.244	0.248
D5	0.37	0.47	0.57	0.015	0.019	0.022
D6	2.49	2.59	2.69	0.098	0.102	0.106
D7	1.76	1.86	1.96	0.069	0.073	0.077



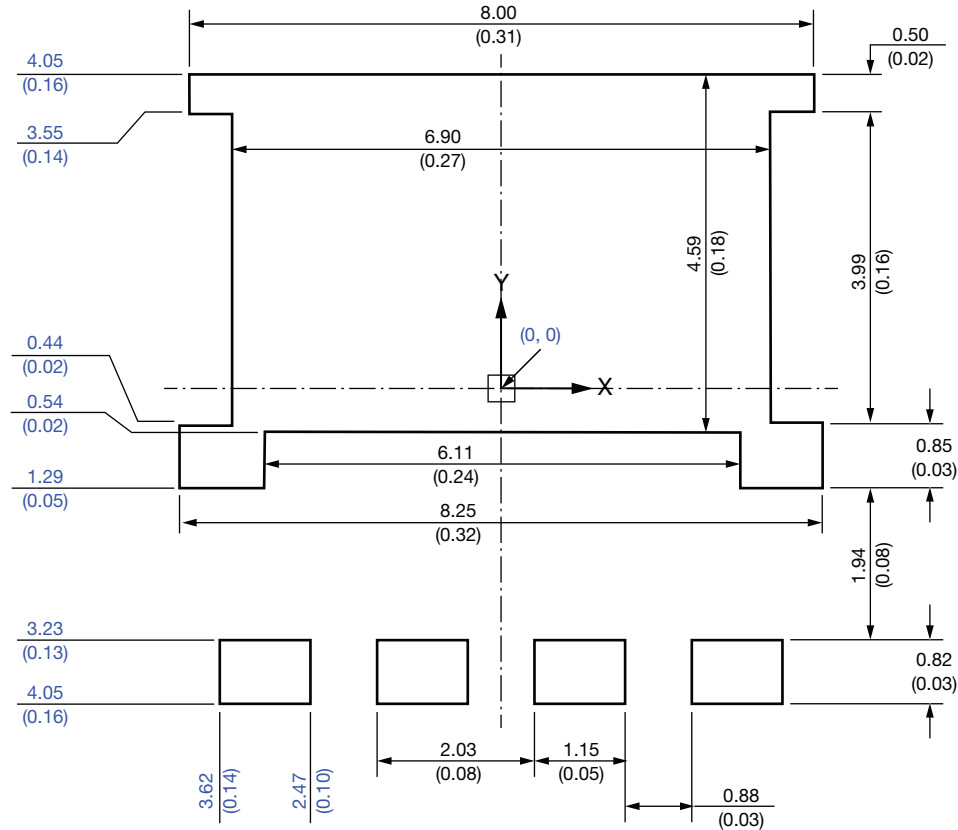
DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
e	1.95	2.00	2.05	0.077	0.079	0.081
E	7.90	8.00	8.10	0.311	0.315	0.319
E1	6.12	6.22	6.32	0.241	0.245	0.249
E2	3.94	4.04	4.14	0.140	0.159	0.163
E3	4.69	4.79	4.89	0.185	0.189	0.193
E4	3.23	3.33	3.43	0.127	0.131	0.135
E5	0.65	0.75	0.85	0.026	0.030	0.033
F	0.00	0.10	0.15	0.000	0.004	0.006
L	0.62	0.72	0.82	0.024	0.028	0.032
L1	0.92	1.07	1.22	0.036	0.042	0.048
K	0.80	0.90	1.00	0.031	0.035	0.039
W	0.30	0.40	0.50	0.012	0.016	0.020
W1	0.30	0.40	0.50	0.012	0.016	0.020
W2	4.39	4.49	4.59	0.173	0.177	0.181
W3	4.54	4.64	4.74	0.179	0.183	0.187
W4	0.32	0.37	0.42	0.013	0.015	0.017
θ	6°	10°	14°	6°	10°	14°

C17-1388-Rev. B, 16-Oct-17  
DWG: 6026





# Recommended Minimum PADS for PowerPAK<sup>®</sup> 8 x 8L Single



Dimensions in millimeters (inches)

**Note**

- Linear dimensions are in black, the same information is provided in ordinate dimensions which are in blue.



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